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**AMENDMENTS TO THE CLAIMS:**

1. (Currently amended) A method of manufacturing a crystal of a III-V compound of a nitride system, the method comprising:

growing a crystal of a III-V compound of the nitride system having a predetermined thickness on a surface of a basal body,

wherein the growth step comprises:

forming a first plurality of nitride patterns of at least one pitch, in one position in a direction of a thickness of the crystal; and

forming a second plurality of nitride patterns of at least one pitch, in another position in the direction of the thickness of the crystal;

wherein the pitch of pattern elements of said first plurality of patterns and the pitch of pattern elements of said second plurality of patterns are different; and

wherein the second plurality of patterns partly overlies and partly does not overlie said first plurality of patterns in the direction of the thickness of the crystal due at least in part to the different pitches.

2. (Previously presented) A method of manufacturing a crystal of a III-V compound of a nitride system as claimed in claim 1,

wherein each of the first and second plurality of patterns takes form in pattern elements arranged in one direction in a plane almost parallel to the surface of the basal body.

3. (Canceled)

4. (Previously presented) A method of manufacturing a crystal of a III-V compound of a nitride system as claimed in claim 2,

wherein a relationship between the pitch of the pattern elements of one of the first plurality of patterns and the pitch of the pattern elements of one of the second plurality of patterns is:

$$0.1 \mu\text{m} < p_1 \times p_2 / |p_2 - p_1| < 5000 \mu\text{m}$$

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